

Ultra High Frequency Matched Pair Transistors

The HFA3134 and HFA3135 are Ultra High Frequency Transistor pairs that are fabricated with Intersil Corporation's complementary bipolar UHF-1X process. The NPN transistors exhibit an f_T of 8.5GHz, while the PNP transistors have an f_T of 7GHz. Both types exhibit low noise, making them ideal for high frequency amplifier and mixer applications.

Both arrays are matched high frequency transistor pairs. The matching simplifies DC bias problems and it minimizes imbalances in differential amplifier configurations. Their high f_T enables the design of UHF amplifiers which exhibit exceptional stability.

Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HFA3134IH96 (04/70)	-40 to 85	6 Ld SOT23 Tape and Reel	P6.064
HFA3134IHZ96 (4Z/Z7) (Note)	-40 to 85	6 Ld SOT23 Tape and Reel (Pb-free)	P6.064
HFA3135IH96 (05/90)	-40 to 85	6 Ld SOT23 Tape and Reel	P6.064
HFA3135IHZ96 (5Z/9Z) (Note)	-40 to 85	6 Ld SOT23 Tape and Reel (Pb-free)	P6.064

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

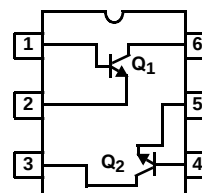
- NPN Transistor (f_T) 8.5GHz
- NPN Current Gain (h_{FE}) 100
- NPN Noise Figure (50Ω) at 1.0GHz. 2.6dB
- PNP Transistor (f_T) 7GHz
- PNP Current Gain (h_{FE}) 57
- PNP Noise Figure (50Ω) at 900MHz 4.6dB
- Small Package (EIAJ-SC74 Compliant) SOT23-6
- Pb-Free Plus Anneal Available (RoHS Compliant)

Applications

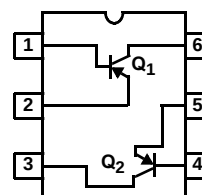
- VHF/UHF Amplifiers
- VHF/UHF Mixers
- IF Converters
- Synchronous Detectors

Pinouts

**HFA3134
(SOT23)
TOP VIEW**



**HFA3135
(SOT23)
TOP VIEW**



HFA3134, HFA3135

Electrical Specifications $T_A = 25^\circ\text{C}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	TYP	MAX	UNITS
DYNAMIC CHARACTERISTICS FOR HFA3134 (NPN)							
Noise Figure	NF	$f = 1.0\text{GHz}$, $I_C = 10\text{mA}$, $1\text{V} \leq V_{CE} \leq 5\text{V}$, $Z_S = 50\Omega$	B	-	2.4	-	dB
		$f = 1.0\text{GHz}$, $I_C = 1\text{mA}$, $1\text{V} \leq V_{CE} \leq 5\text{V}$, $Z_S = 50\Omega$	B	-	2.6	-	dB
Current Gain-Bandwidth Product (Note 5)	f_T	$I_C = 10\text{mA}$, $V_{CE} = 5\text{V}$	B	-	8.5	-	GHz
		$I_C = 1\text{mA}$, $V_{CE} = 5\text{V}$	B	-	3	-	GHz
Power Gain-Bandwidth Product	f_{MAX}	$I_C = 10\text{mA}$, $V_{CE} = 5\text{V}$	B	-	7.5	-	GHz
Base to Emitter Capacitance		$V_{BE} = -0.5\text{V}$	B	-	600	-	fF
Collector to Base Capacitance		$V_{CB} = 3\text{V}$	B	-	500	-	fF

Electrical Specifications $T_A = 25^\circ\text{C}$

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	TYP	MAX	UNITS
DC CHARACTERISTICS FOR HFA3135 (PNP)							
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	A	12	21	-	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -100\mu\text{A}$, $I_B = 0$	A	4	14	-	V
	$V_{(BR)CER}$	$I_C = -100\mu\text{A}$, $R_B = 10\text{k}\Omega$	A	11	23	-	V
Emitter to Base Breakdown Voltage (Note 4)	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	B	-	5	-	V
Collector-Cutoff-Current	I_{CEO}	$V_{CE} = -6\text{V}$, $I_B = 0$	A	-5	-	5	nA
Collector-Cutoff-Current	I_{CBO}	$V_{CB} = -8\text{V}$, $I_E = 0$	A	-5	-	5	nA
Emitter-Cutoff-Current	I_{EBO}	$V_{EB} = -1\text{V}$, $I_C = 0$	B	-	TBD	-	pA
Collector to Collector Leakage			B	-	1	-	nA
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$	A	-	150	250	mV
Base to Emitter Voltage	V_{BE}	$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$	A	-	850	1000	mV
Q ₁ to Q ₂ Base to Emitter Voltage Match	ΔV_{BE}	$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$	A	-	1	6	mV
		$I_C = -1\text{mA}$, $V_{CE} = -2\text{V}$	A	-	1	6	mV
		$I_C = -0.1\text{mA}$, $V_{CE} = -2\text{V}$	A	-	2	6	mV
DC Forward-Current Transfer Ratio	h_{FE}	$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$	A	15	40	125	
		$I_C = -1\text{mA}$, $V_{CE} = -2\text{V}$	A	15	47	125	
		$I_C = -0.1\text{mA}$, $V_{CE} = -2\text{V}$	A	15	52	125	
		$I_C = -10\text{mA}$, $V_{CE} = -5\text{V}$	A	15	47	125	
		$I_C = -1\text{mA}$, $V_{CE} = -5\text{V}$	A	15	53	125	
		$I_C = -0.1\text{mA}$, $V_{CE} = -5\text{V}$	A	15	57	125	
Q ₁ to Q ₂ Current Gain Match	Δh_{FE}	$-1\text{mA} \leq I_C \leq -10\text{mA}$, $-1\text{V} \leq V_{CE} \leq -5\text{V}$	A	-	1	8	%
Early Voltage	V_A	$I_C = -1\text{mA}$, $\Delta V_{CE} = -3\text{V}$	A	15	24	-	V
Base to Emitter Voltage Drift		$I_C = -10\text{mA}$	C	-	-1.4	-	mV/ $^\circ\text{C}$

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Electrical Specifications $T_A = 25^\circ\text{C}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	TYP	MAX	UNITS
DYNAMIC CHARACTERISTICS FOR HFA3135 (PNP)							
Noise Figure	NF	$f = 900\text{MHz}$, $I_C = -10\text{mA}$, $-1\text{V} \leq V_{CE} \leq -5\text{V}$, $Z_S = 50\Omega$	B	-	5.2	-	dB
		$f = 900\text{MHz}$, $I_C = -1\text{mA}$, $-1\text{V} \leq V_{CE} \leq -5\text{V}$, $Z_S = 50\Omega$	B	-	4.6	-	dB
Current Gain-Bandwidth Product	f_T	$I_C = -10\text{mA}$, $V_{CE} = -5\text{V}$	B	-	7	-	GHz
Power Gain-Bandwidth Product	f_{MAX}	$I_C = -10\text{mA}$, $V_{CE} = -5\text{V}$	B	-	TBD	-	GHz
Base to Emitter Capacitance		$V_{BE} = 0.5\text{V}$	B	-	550	-	fF
Collector to Base Capacitance		$V_{CB} = -3\text{V}$	B	-	400	-	fF

NOTES:

- Test Level: A. Production Tested; B. Typical or Guaranteed Limit Based on Characterization; C. Design Typical for Information Only.
- Measuring V_{EBO} can degrade the transistor h_{FE} and h_{FE} match.
- See Typical Performance Curves for more information.

Typical Performance Curves $T_A = 25^\circ\text{C}$, Unless Otherwise Specified

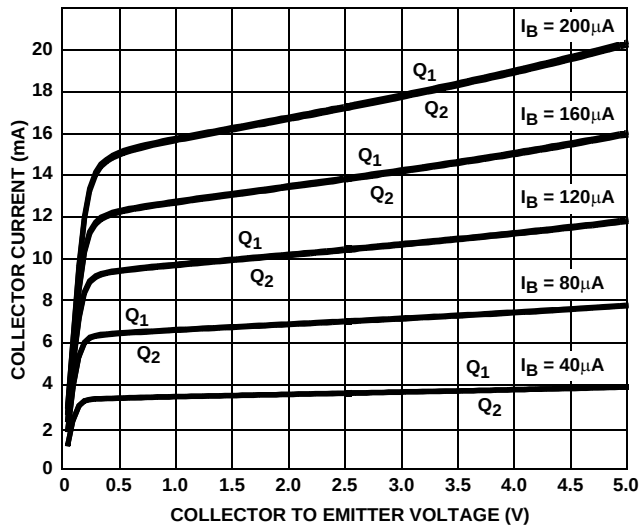


FIGURE 1. NPN COLLECTOR CURRENT vs COLLECTOR TO EMITTER VOLTAGE

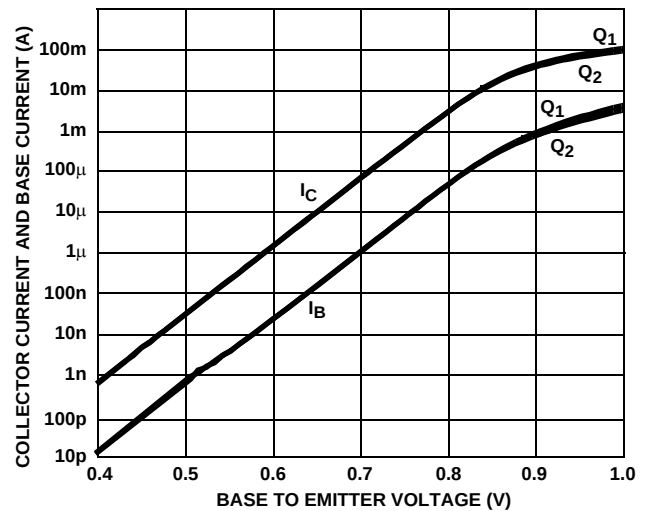


FIGURE 2. NPN COLLECTOR AND BASE CURRENTS vs BASE TO EMITTER VOLTAGE

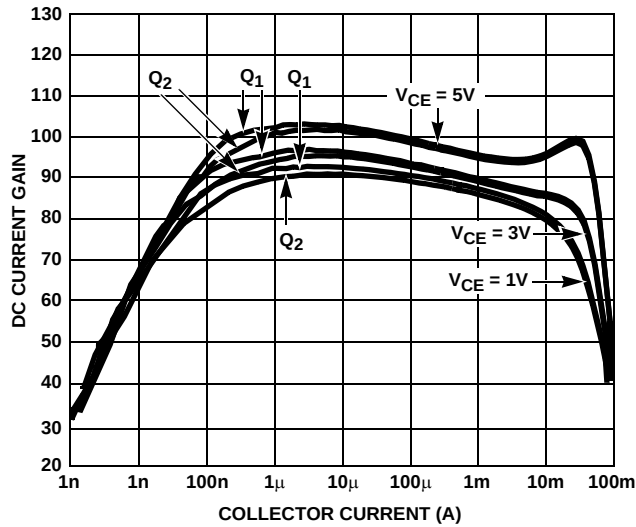
Typical Performance Curves $T_A = 25^\circ\text{C}$, Unless Otherwise Specified (Continued)

FIGURE 3. NPN DC CURRENT GAIN vs COLLECTOR CURRENT

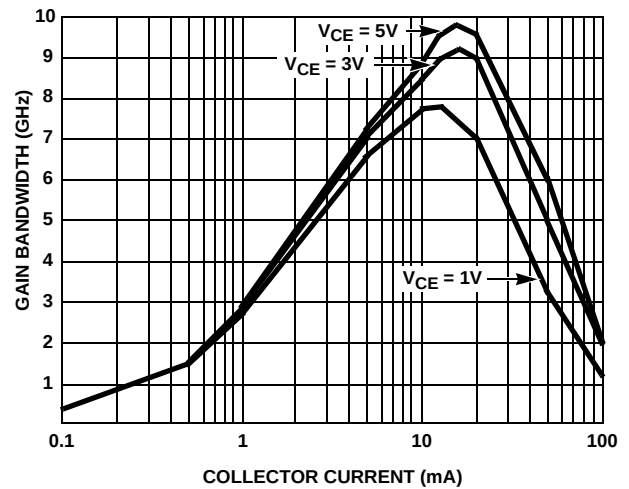


FIGURE 4. NPN GAIN BANDWIDTH PRODUCT vs COLLECTOR CURRENT

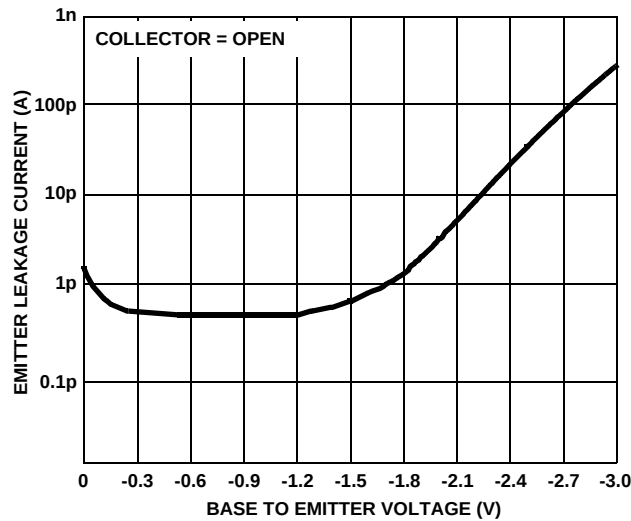


FIGURE 5. NPN EMITTER CUTOFF CURRENT vs BASE TO EMITTER VOLTAGE

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